



P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	Rds(on) max	Package	I _D T _A = +25°C
	38mΩ @ V _{GS} = -10V		-4.3A
-20V	43mΩ @ V _{GS} = -4.5V	SOT23	-4.0A
	75mΩ @ V _{GS} = -2.5V		-2.8A

Description

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Load Switch
- Power Management Functions
- Motor Control

Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMP2100UQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

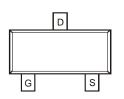
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (§3)
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)



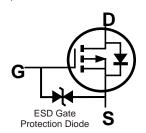


SOT23

Top View



Top View Pin Configuration



Equivalent Circuit (Note 4)

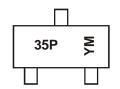
Ordering Information (Note 5)

I	Part Number	Compliance	Case	Packaging
	DMP2100UQ-7	Automotive	SOT23	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. The ESD gate protection diode is only designed to protect against ESD events. No gate-source voltage greater than the maximum V_{GSS} rating (given on page 2) can be applied.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



35P = Product Type Marking Code YM = Date Code Marking Y = Year (ex: G = 2019) M = Month (ex: 9 = September)

Date Code Key

Year	2008	~	2017	2018	3 201	19 20	20 2	2021	2022	2023	2024	2025
Code	V	~	Е	F	G	i [Н	1	J	K	L	М
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		VDSS	-20	V	
Gate-Source Voltage (Note 6)		Vgss	±10	V	
Continuous Davis Courset (Nate 0) V	Steady State	T _A = +25°C T _A = +70°C	lD	-4.3 -3.4	А
Continuous Drain Current (Note 8) V _{GS} = -10V	t<5s	T _A = +25°C T _A = +70°C	I _D	-5.5 -4.3	А
Maximum Continuous Body Diodes Forward Curr	ent (Note 8	Is	-2	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1	%)	I _{DM}	-30	Α	
Pulsed Body Diodes Forward Current (10µs Pulse	e, Duty Cyc	Ism	-30	A	

Thermal Characteristics

Characteristic	Symbol	Value	Unit	
Total Bower Dissipation (Note 7)	T _A = +25°C	Ĺ	0.8	W
Total Power Dissipation (Note 7)	$T_A = +70^{\circ}C$	P_{D}	0.5	
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	Reja	161	°C/W
memal Resistance, Junction to Ambient (Note 1)	t<5s	Көја	96	
Total Power Dissipation (Note 8)	$T_A = +25^{\circ}C$	D-	1.3	°C/W
Total Fower Dissipation (Note 6)	$T_A = +70^{\circ}C$	P _D	0.8	
Thermal Resistance, Junction to Ambient (Note 8)	Steady State	Dov	99	
mermal Resistance, Junction to Ambient (Note 6)	t<5s	Reja	60	
Thermal Resistance, Junction to Case (Note 8)	$R_{ heta JC}$	15		
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

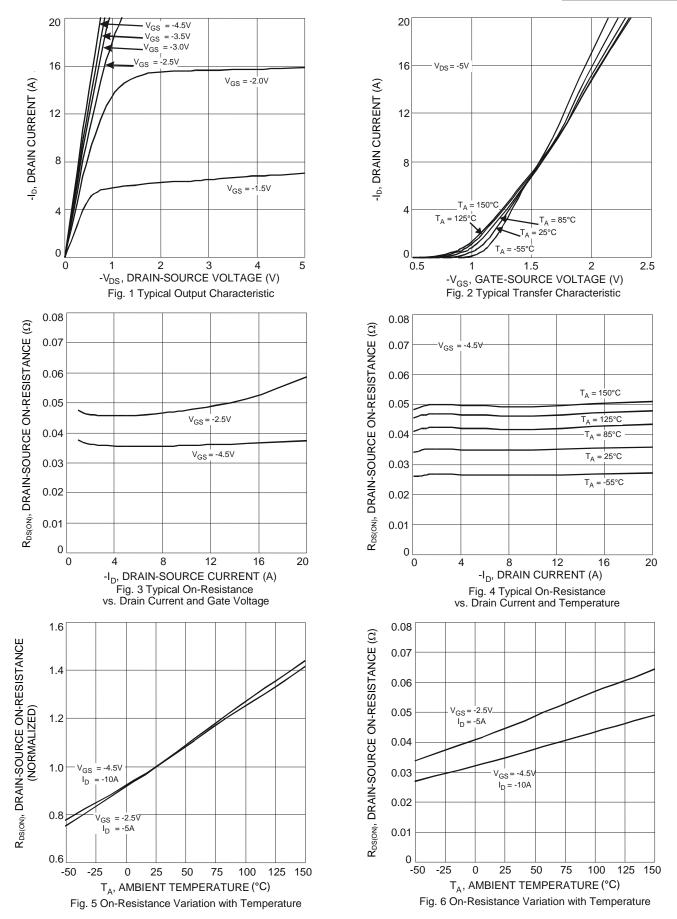
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	IDSS	_	_	-1	μΑ	V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage	Igss	_	_	±10	μΑ	$V_{GS} = \pm 8V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	Vgs(TH)	-0.3	_	-1.4	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$
		_	25	38		$V_{GS} = -10V, I_D = -3.5A$
Static Drain-Source On-Resistance	D	_	29	43	mΩ	VGS = -4.5V, ID = -3A
Static Diain-Source On-Resistance	RDS(ON)	_	37	75	11122	$V_{GS} = -2.5V, I_{D} = -1A$
		_	47	_		V _G S = -1.8V, I _D = -0.5A
Forward Transfer Admittance	Y _{fs}	_	3		S	V _{DS} = -5V, I _D = -4A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	Ciss	l	216		pF	45// // 0//
Output Capacitance	Coss		90	_	pF	V _{DS} = -15V, V _{GS} = 0V -f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	24	_	pF	1 = 1.0IVII IZ
Gate Resistance	Rg	_	250	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1.0MHz$
SWITCHING CHARACTERISTICS (Note 10)						
Total Gate Charge	Qg		9.1	_	nC	15)/ // 10)/
Gate-Source Charge	Q_{gs}	_	1.6	_	nC	Vgs = -4.5V, Vps = -10V
Gate-Drain Charge	Q_{gd}	_	2.0	_	nC	ID = -4A
Turn-On Delay Time	t _{D(ON)}	_	80		ns	
Turn-On Rise Time	t _R	ı	155	_	ns	V _{DS} = -10V, V _{GS} = -4.5V,
Turn-Off Delay Time	tD(OFF)	_	688	_	ns	$R_D = 2.5\Omega$, $R_G = 3.0\Omega$
Turn-Off Fall Time	t _F		423	_	ns	

Notes:

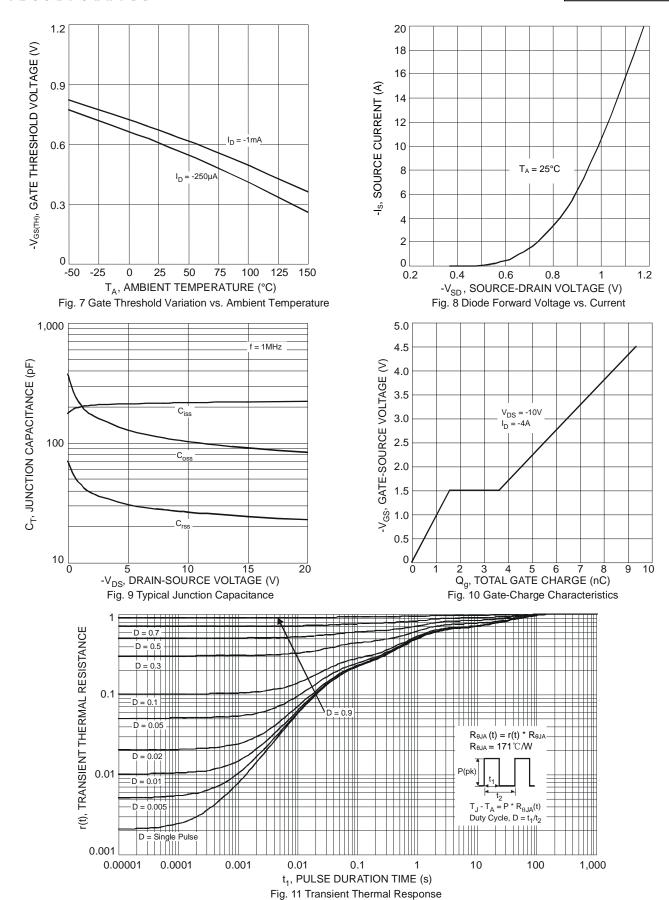
- 6. AEC-Q101 V_{GS} maximum is $\pm 9.6 V$.
- 7. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

 8. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
- Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.







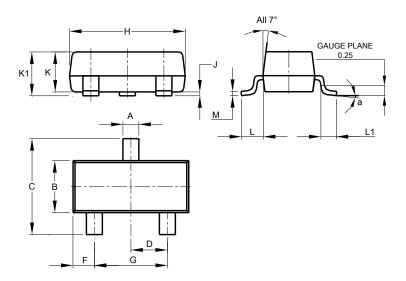




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

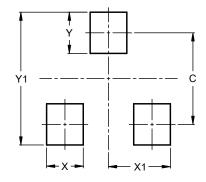


SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	B 1.20		1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
7	0.013	0.10	0.05				
K 0.890		1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
M	0.085	0.150	0.110				
а	0°	8°					
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Υ	0.9
Y1	2.9



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